

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE
APPLICATION FOR UNITED STATES LETTERS PATENT

Title:

**CLEANING SOLUTION FOR PHOTORESIST AND METHOD FOR
FORMING PATTERN USING THE SAME**

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CLEANING SOLUTION FOR PHOTORESIST AND METHOD FOR FORMING PATTERN USING THE SAME

Technical Field

5 Cleaning solutions for photoresist are disclosed which are useful for
cleaning a semiconductor substrate in the last step of development when photoresist
patterns are formed. More specifically, a cleaning solution for photoresist comprising
H₂O as a primary solvent, a surfactant of phosphate-alcoholamine salt as an additive
and an alcohol compound, and a method for forming patterns using the same are
10 disclosed.

Description of the Related Art

 As semiconductor devices become smaller, the aspect ratio of the
photoresist patterns (i.e. the ratio of the thickness of photoresist, or height to the
linewidth of formed pattern) increases.

15 When the height of formed photoresist patterns extends beyond critical
height, capillary force exceeds elasticity of photoresist, thereby resulting in collapse
of patterns during a cleaning process.

 In order to overcome this problem, adhesive force between underlying
layers and photoresist is enhanced by increasing inner elasticity of photoresist or
20 decreasing surface tension thereof.

 Generally, a method of forming photoresist patterns on semiconductor
substrates comprises the steps of: forming an underlying layer on a semiconductor
substrate; forming a photoresist film on the underlying layer; and exposing a portion
of the underlying layer by exposing and developing processes to form a photoresist
25 pattern. In case of a positive photoresist, the photoresist film of an exposing region is
removed by developing solution to form a photoresist pattern.

 The last step of the above method is a cleaning process of removing
the residual photoresist film by spraying distilled water from spin equipment while the
semiconductor substrate is spun. In this process, the pattern is collapsed due to high
30 surface tension of the distilled water.

 Conventionally, U.S. Patent No. 5,374,502 discloses that the collapse
of photoresist patterns having high aspect ratios can be prevented by using a cleaning

solution including tert-amyl alcohol, 2-methyl-1-butanol, 1-butanol, tert-butyl alcohol, 3-pentanol and isobutyl alcohol.

In addition, U.S. Patent No. 5,474,877 discloses that the collapse of photoresist patterns can be prevented by using a cleaning solution whose surface tension is lowered by heat. However, neither solution provided by the prior art is ideal and therefore there is a continuing need for improved cleaning solutions that address the problems of high aspect ratio photoresist patterns.

SUMMARY OF THE DISCLOSURE

Accordingly, cleaning solutions for photoresist patterns is disclosed whose surface tension is lowered to prevent collapse of photoresist patterns in the last development process of removing the residual photoresist film. Also, methods for forming patterns using the same are disclosed.

BRIEF DESCRIPTION OF THE DRAWINGS

Fig. 1 is a photograph of a photoresist pattern obtained from Example

9.

Fig. 2 is a photograph of a photoresist pattern obtained from Example

10.

Fig. 3 is a photograph of a photoresist pattern obtained from Example

11.

Fig. 4 is a photograph of a photoresist pattern obtained from Example

12.

Fig. 5 is a photograph of a photoresist pattern obtained from Example

13.

Fig. 6 is a photograph of a photoresist pattern obtained from Example

14.

Fig. 7 is a photograph of a photoresist pattern obtained from Example

15.

Fig. 8 is a photograph of a photoresist pattern obtained from Example

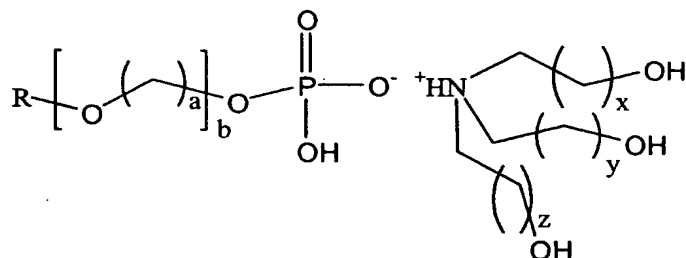
16.

Fig. 9 is a photograph of a photoresist pattern obtained from Comparative Example 2.

DETAILED DESCRIPTION OF THE PRESENTLY PREFERRED EMBODIMENTS

A cleaning solution for photoresist comprises H₂O as a solution and a compound represented by following Formula 1 as a surfactant:

Formula 1



wherein

R is C₂-C₂₀ alkyl or C₆-C₂₅ alkyl aryl;

x, y and z individually are an integer ranging from 0 to 10;

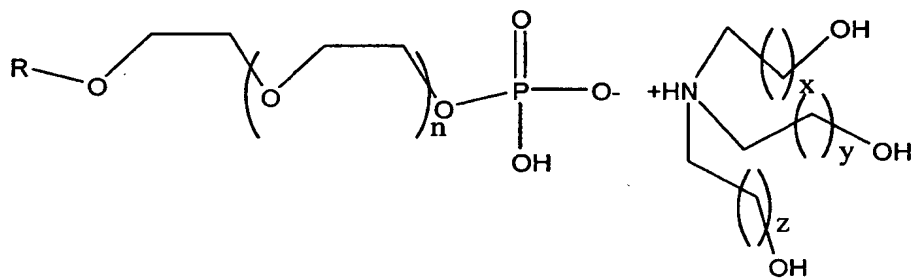
a is 2 or 3; and

b is an integer ranging from 2 to 50.

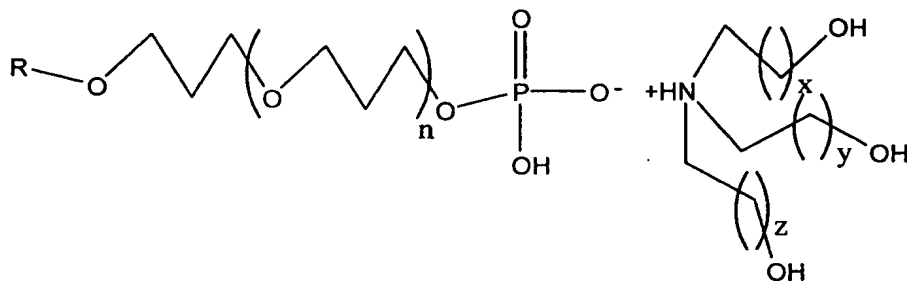
The compound of Formula 1 is water-soluble since which is salt. Also, the compound of Formula 1, which includes both a hydrophilic group such as a hydroxyl group and a hydrophobic group such as an alkyl group having a long chain in one molecule, remarkably lowers surface tension.

Preferably, the compound of Formula 1 which is phosphate-alcoholamine salt is represented by Formula 2 or Formula 3:

Formula 2



Formula 3



wherein

R is C₂-C₂₀ alkyl or C₆-C₂₅ alkyl aryl;

5 x, y and z individually are an integer ranging from 0 to 10; and
n is an integer ranging from 1 to 49.

In the compound of Formula 2 or Formula 3, R is preferably C₆-C₁₄ alkyl or C₁₂-C₂₀ alkyl aryl, and more preferably selected from the group consisting of octyl, octyl phenyl, nonyl, nonyl phenyl, decyl, decyl phenyl, undecyl, undecyl
10 phenyl, dodecyl and dodecyl phenyl, n is an integer ranging from 5 to 10, and x, y and z individually are an integer ranging from 0 to 2.

More specifically, the compound of Formula 2 is selected from the group consisting of compound wherein R is nonyl, x, y and z are 1, and n is 7; compound wherein R is octyl, x, y and z are 1, and n is 7; compound wherein R is
15 dodecyl, x, y and z are 0, and n is 7; and compound wherein R is octyl phenyl, x, y and z are 1, and n is 3.

Also, the compound of Formula 3 is selected from the group consisting of compound wherein R is nonyl, x, y and z are 1, and n is 7; compound wherein R is octyl, x, y and z are 1, and n is 7; compound wherein R is dodecyl, x, y and z are 0,
20 and n is 7; and compound wherein R is octyl phenyl, x, y and z are 1, and n is 3.

The water of the disclosed cleaning solution is preferably distilled water.

The disclosed water further comprises an alcohol.

The above alcohol comprises C₁-C₁₀ alkyl alcohol or C₁-C₁₀
25 alkoxyalkyl alcohol. Preferably, the C₁-C₁₀ alkyl alcohol is selected from the group consisting of methanol, ethanol, propanol, isopropanol, n-butanol, sec-butanol, t-butanol, 1-pentanol, 2-pentanol, 3-pentanol, 2,2-dimethyl-1-propanol and mixtures thereof, and the C₁-C₁₀ alkoxyalkyl alcohol is selected from the group consisting of 2-

methoxyethanol, 2-(2-methoxyethoxy)ethanol, 1-methoxy-2-propanol, 3-methoxy-1,2-propandiol and mixtures thereof.

In the disclosed cleaning solution, the compound of Formula 1, which is a surfactant, is present in an amount ranging from 0.001 to 2 wt% based on the total weight of said solution, and the alcohol is present in an amount ranging from 0 to 20 wt% based on the total weight of said solution.

When the compound of Formula 1 is present in the amount of less than 0.001 wt%, the effect of lowering surface tension is degraded. When the compound of Formula 1 is present in the amount of more than 2 wt%, the effect of lowering surface tension is also degraded, and the residual compound of Formula 1 remains on the wafer.

In addition, when the alcohol is present in the amount of more than 20 wt%, the alcohol dissolves photoresist materials, thereby collapsing patterns.

Specifically, the compound of Formula 2 is present in an amount ranging from 0.001 to 2 wt%, more preferably, from 0.01 to 1 wt% based on the total weight of said solution, and the alcohol is present in an amount ranging from 0 to 20 wt%, more preferably, from 0.01 to 10 wt% based on the total weight of said solution.

The compound of Formula 3, which is a surfactant, is present in an amount ranging from 0.001 to 2 wt%, more preferably, from 0.001 to 1 wt% based on the total weight of said solution, and the alcohol is present in an amount ranging from 0 to 10 wt%, more preferably, from 0.001 to 5 wt% based on the total weight of said solution.

The disclosed cleaning solution is manufactured by filtering the resulting mixture of the distilled water, the compound of Formula 1 and the alcohol with 0.2 μ m filter.

A method for forming a photoresist pattern comprises:

- (a) preparing a semiconductor substrate on which an underlying layer is formed;
- (b) coating a photoresist on the underlying layer to form a photoresist film;
- (c) exposing the photoresist film to light;
- (d) developing the exposed photoresist film; and
- (e) cleaning the resulting structure using a disclosed cleaning solution.

The above method further comprises soft baking step before part (c) or post baking step after part (c). Preferably, the bake process is performed at a temperature ranging from 70 to 200°C.

5 In the above the exposure step, the source of the light is preferably selected from the group consisting of KrF (248 nm), ArF (193 nm), VUV (157 nm), EUV (13 nm), E-beam, X-ray and ion-beam. The exposure step is preferably performed at exposure energy ranging from 0.1 to 50 mJ/cm².

10 The above development step (d) is performed with an alkaline developing solution which is preferably TMAH aqueous solution ranging from 0.01 to 5 wt%.

As described above, the collapse of photoresist patterns can be prevented by performing the cleaning process using the disclosed cleaning solution including the compound of Formula 1 which is a surfactant to lower surface tension of the cleaning solution.

15 Additionally, a semiconductor device manufactured according to the process described above is disclosed.

The disclosed cleaning solution for photoresist will be described in more details referring to examples below, when are not intended to be limiting.

20 Example 1. Preparation of Cleaning Solution and Measurement of Surface Tension

The compound of Formula 2 wherein R is nonyl, x, y and z are 1, respectively, and n is 7 (0.3 g), methanol (1 g) and distilled water (99 g) were stirred for 1 minute. The resulting mixture was filtered through a 0.2µm filter to obtain a disclosed cleaning solution. The surface tension of the disclosed cleaning solution measured by a KRUSS K9 tension meter of measurement equipment was 31N m/m².

Example 2. Preparation of Cleaning Solution and Measurement of Surface Tension

30 The compound of Formula 2 wherein R is octyl, x, y and z are 1, respectively, and n is 7 (0.3 g), methanol (1 g) and distilled water (99 g) were stirred for 1 minute. The resulting mixture was filtered through a 0.2 µm filter to obtain a disclosed cleaning solution. The surface tension of the disclosed cleaning solution measured by a KRUSS K9 was 32N m/m².

Example 3. Preparation of Cleaning Solution and Measurement of Surface Tension

The compound of Formula 2 wherein R is dodecyl, x, y and z are 0, respectively, and n is 7 (0.3 g), isopropanol (1 g) and distilled water (99 g) were stirred for 1 minute. The resulting mixture was filtered through a 0.2 μm filter to obtain a disclosed cleaning solution. The surface tension of the disclosed cleaning solution measured by a KRUSS K9 was 28N m/m².

Example 4. Preparation of Cleaning Solution and Measurement of Surface Tension

The compound of Formula 2 wherein R is octyl phenyl, x, y and z are 1, respectively, and n is 3 (0.3 g), isopropanol (1 g) and distilled water (99 g) were stirred for 1 minute. The resulting mixture was filtered through a 0.2 μm filter to obtain a disclosed cleaning solution. The surface tension of the disclosed cleaning solution measured by a KRUSS K9 was 29N m/m².

Example 5. Preparation of Cleaning Solution and Measurement of Surface Tension

The compound of Formula 3 wherein R is nonyl, x, y and z are 1, respectively, and n is 7 (0.3 g), methanol (1 g) and distilled water (99 g) were stirred for 1 minute. The resulting mixture was filtered through a 0.2 μm filter to obtain a disclosed cleaning solution. The surface tension of the disclosed cleaning solution measured by a KRUSS K9 was 34N m/m².

Example 6. Preparation of Cleaning Solution and Measurement of Surface Tension

The compound of Formula 3 wherein R is octyl, x, y and z are 1, respectively, and n is 7 (0.3 g), methanol (1 g) and distilled water (99 g) were stirred for 1 minute. The resulting mixture was filtered through a 0.2 μm filter to obtain a disclosed cleaning solution. The surface tension of the disclosed cleaning solution measured by a KRUSS K9 was 37N m/m².

Example 7. Preparation of Cleaning Solution and Measurement of Surface Tension

The compound of Formula 3 wherein R is dodecyl, x, y and z are 0, respectively, and n is 7 (0.3 g), isopropanol (1 g) and distilled water (99 g) were stirred for 1 minute. The resulting mixture was filtered through a 0.2 μm filter to obtain a disclosed cleaning solution. The surface tension of the disclosed cleaning solution measured by a KRUSS K9 was 33N m/m².

Example 8. Preparation of Cleaning Solution and Measurement of Surface Tension

The compound of Formula 3 wherein R is octyl phenyl, x, y and z are 1, respectively, and n is 3 (0.3 g), isopropanol (1 g) and distilled water (99 g) were stirred for 1 minute. The resulting mixture was filtered through a 0.2 μm filter to obtain a disclosed cleaning solution. The surface tension of the disclosed cleaning solution measured by a KRUSS K9 was 37N m/m².

Comparative Example 1. Measurement of Surface Tension of Distilled Water

The surface tension of the distilled water as measured by the KRUSS K9 was 73N m/m².

Example 9. Formation of Photoresist Pattern

After an underlying layer was formed on a silicon wafer treated with hexamethyldisilazane (HMDS), a photoresist comprising methacrylate type compound, sold under the designation "AX1020P" by Clariant, was spin-coated on the silicon wafer at a thickness 2400 Å to form a photoresist film, and soft-baked at 130°C for 90 seconds. After soft-baking, the photoresist film was exposed to light using an ArF laser exposer, and then post-baked at 130°C for 90 seconds. When the post-baking was completed, it was developed in 2.38 wt% aqueous TMAH solution for 30 seconds. While the silicon wafer was spun, the silicon wafer was cleaned by spraying the cleaning solution (30 ml) obtained from Example 1 from the spin equipment and then dehydrated, to obtain 90 nm L/S photoresist pattern (see Fig. 1).

Example 10. Formation of Photoresist Pattern

The procedure of Example 9 was repeated using the cleaning solution of Example 2 instead of the cleaning solution of Example 1 to obtain 90 nm L/S photoresist pattern (see Fig. 2).

Example 11. Formation of Photoresist Pattern

The procedure of Example 9 was repeated using the cleaning solution of Example 3 instead of the cleaning solution of Example 1 to obtain 90 nm L/S photoresist pattern (see Fig. 3).

Example 12. Formation of Photoresist Pattern

The procedure of Example 9 was repeated using the cleaning solution of Example 4 instead of the cleaning solution of Example 1 to obtain 90 nm L/S photoresist pattern (see Fig. 4).

Example 13. Formation of Photoresist Pattern

The procedure of Example 9 was repeated using the cleaning solution of Example 5 instead of the cleaning solution of Example 1 to obtain 90 nm L/S photoresist pattern (see Fig. 5).

5 Example 14. Formation of Photoresist Pattern

The procedure of Example 9 was repeated using the cleaning solution of Example 6 instead of the cleaning solution of Example 1 to obtain 90 nm L/S photoresist pattern (see Fig. 6).

Example 15. Formation of Photoresist Pattern

10 The procedure of Example 9 was repeated using the cleaning solution of Example 7 instead of the cleaning solution of Example 1 to obtain 90 nm L/S photoresist pattern (see Fig. 7).

Example 16. Formation of Photoresist Pattern

15 The procedure of Example 9 was repeated using the cleaning solution of Example 8 instead of the cleaning solution of Example 1 to obtain 90 nm L/S photoresist pattern (see Fig. 8).

Comparative Example 2. Formation of Photoresist Pattern

20 The procedure of Example 9 was repeated using the distilled water instead of the cleaning solution of Example 1 to obtain a photoresist pattern. As a result, the photoresist pattern collapsed (see Fig. 9).

As shown in the above Examples, the collapse of patterns can be avoided by using the disclosed cleaning solution in the last step of the development because the disclosed cleaning solution has a lower surface tension than distilled water which has been used in conventional cleaning solutions. Accordingly, the disclosed cleaning solution may enable stabilization of development processes for forming ultrafine photoresist patterns of less than 130 nm.

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